

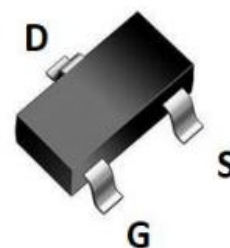
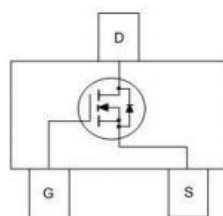


安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

FS8N02

SOT-23-3L 20V N Channel Enhancement 沟道增强型 MOS Field Effect Transistor 场效应管



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	20	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 12	V
Drain Current (continuous)漏极电流-连续	I_D (at $T_A = 25^\circ C$)	8	A
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	25	A
Total Device Dissipation 总耗散功率	P_D (at $T_A = 25^\circ C$)	1500	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	83.3	$^\circ C/W$
Junction/Storage Temperature 结温/储存温度	T_J, T_{stg}	-55~150	$^\circ C$

■ Device Marking 产品字标

FS8N02=2208



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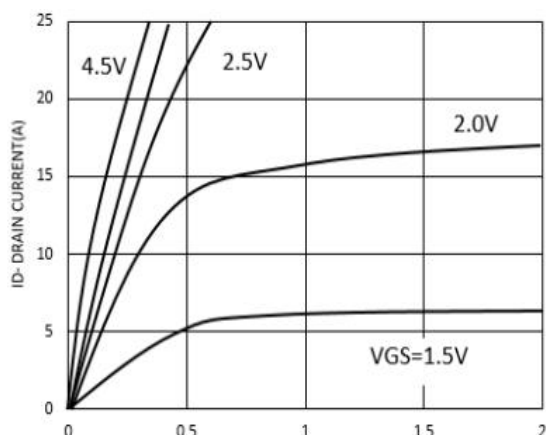
FS8N02

■ Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

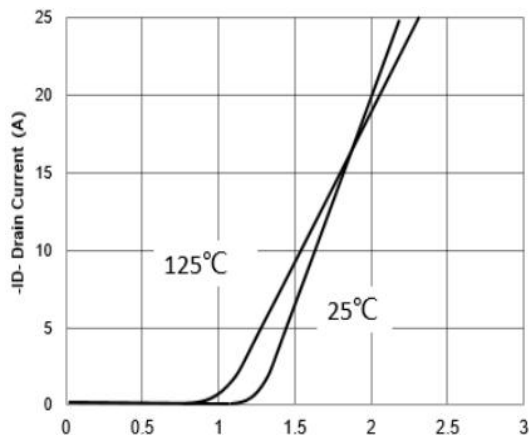
Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压($I_D = 250\mu\text{A}, V_{GS}=0\text{V}$)	BV_{DSS}	20	—	—	V
Gate Threshold Voltage 栅极开启电压($I_D = 250\mu\text{A}, V_{GS} = V_{DS}$)	$V_{GS(th)}$	0.5	0.75	1.2	V
Zero Gate Voltage Drain Current 零栅压漏极电流($V_{GS}=0\text{V}, V_{DS}=20\text{V}$)	I_{DSS}	—	—	1	μA
Gate Body Leakage 栅极漏电流($V_{GS}=\pm 12\text{V}, V_{DS}=0\text{V}$)	I_{GSS}	—	—	± 100	nA
Static Drain-Source On-State Resistance 静态漏源导通电阻($I_D=7\text{A}, V_{GS}=4.5\text{V}$) ($I_D=5\text{A}, V_{GS}=2.5\text{V}$)	$R_{DS(ON)}$	—	11 14	14 22.5	$\text{m}\Omega$
Diode Forward Voltage Drop 内附二极管正向压降($I_{SD}=2.6\text{A}, V_{GS}=0\text{V}$)	V_{SD}	—	—	1.2	V
Input Capacitance 输入电容 ($V_{GS}=0\text{V}, V_{DS}=10\text{V}, f=1\text{MHz}$)	C_{ISS}	—	1100	—	pF
Common Source Output Capacitance 共源输出电容($V_{GS}=0\text{V}, V_{DS}=10\text{V}, f=1\text{MHz}$)	C_{OSS}	—	182	—	pF
Reverse Transfer Capacitance 反馈电容 ($V_{GS}=0\text{V}, V_{DS}=10\text{V}, f=1\text{MHz}$)	C_{RSS}	—	164	—	pF
Total Gate Charge 栅极电荷密度 ($V_{DS}=10\text{V}, I_D=4\text{A}, V_{GS}=4.5\text{V}$)	Q_g	—	15	—	nC
Gate Source Charge 栅源电荷密度 ($V_{DS}=10\text{V}, I_D=4\text{A}, V_{GS}=4.5\text{V}$)	Q_{gs}	—	2	—	nC
Gate Drain Charge 栅漏电荷密度 ($V_{DS}=10\text{V}, I_D=4\text{A}, V_{GS}=4.5\text{V}$)	Q_{gd}	—	5	—	nC
Turn-ON Delay Time 开启延迟时间 ($V_{DS}=10\text{V}, I_D=4\text{A}, R_{GEN}=3\Omega, V_{GS}=4.5\text{V}$)	$t_{d(on)}$	—	9	—	ns
Turn-ON Rise Time 开启上升时间 ($V_{DS}=10\text{V}, I_D=4\text{A}, R_{GEN}=3\Omega, V_{GS}=4.5\text{V}$)	t_r	—	25	—	ns
Turn-OFF Delay Time 关断延迟时间 ($V_{DS}=10\text{V}, I_D=4\text{A}, R_{GEN}=3\Omega, V_{GS}=4.5\text{V}$)	$t_{d(off)}$	—	37	—	ns
Turn-OFF Fall Time 关断下降时间 ($V_{DS}=10\text{V}, I_D=4\text{A}, R_{GEN}=3\Omega, V_{GS}=4.5\text{V}$)	t_f	—	14	—	ns

■ Typical Characteristic Curve 典型特性曲线



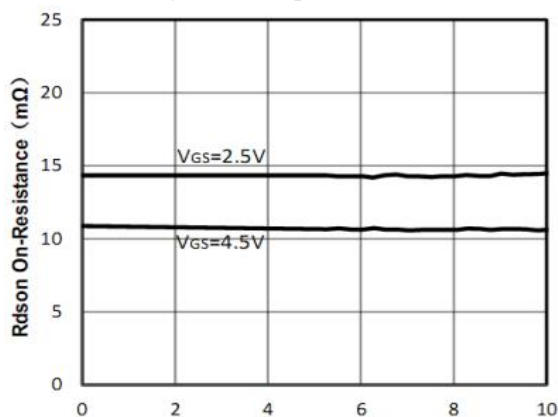
-V_{DS} Drain-Source Voltage (V)

Figure 1: Output Characteristics



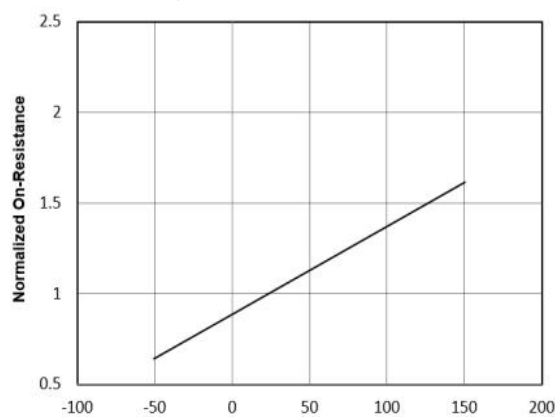
-V_{GS} Gate-Source Voltage (V)

Figure 2: Transfer Characteristics



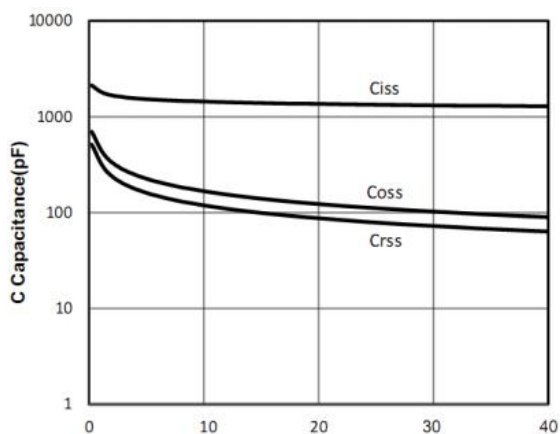
-I_D Drain Current (A)

Figure 3: On-Resistance vs. Drain Current



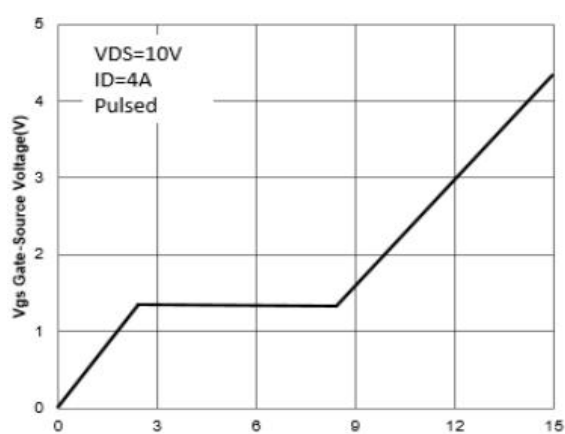
T_J Junction Temperature (°C)

Figure 4: On-Resistance vs. Temperature



V_{DS} Drain-Source Voltage (V)

Figure 5: Capacitance Characteristics



Q_g Gate Charge (nC)

Figure 6: Gate-Charge Characteristics

■ Typical Characteristic Curve 典型特性曲线

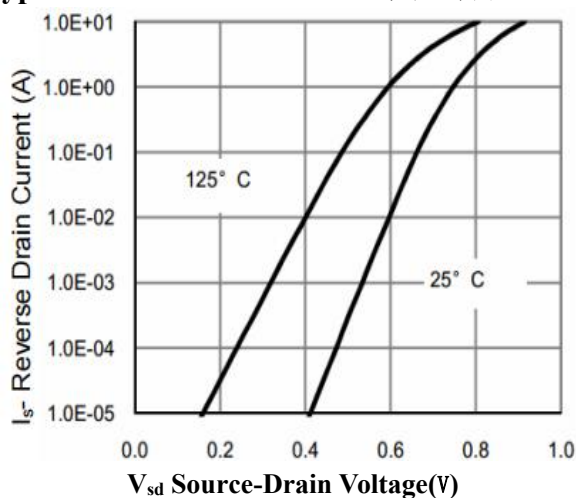


Figure 7: Body Diode Characteristics

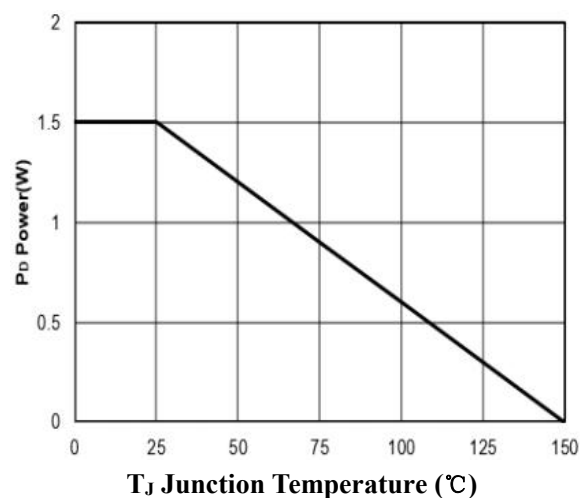


Figure 8: Power Dissipation

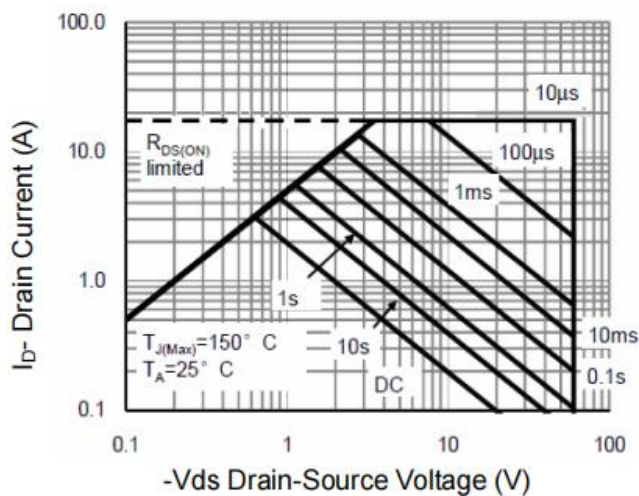


Figure 9: Safe Operating Area

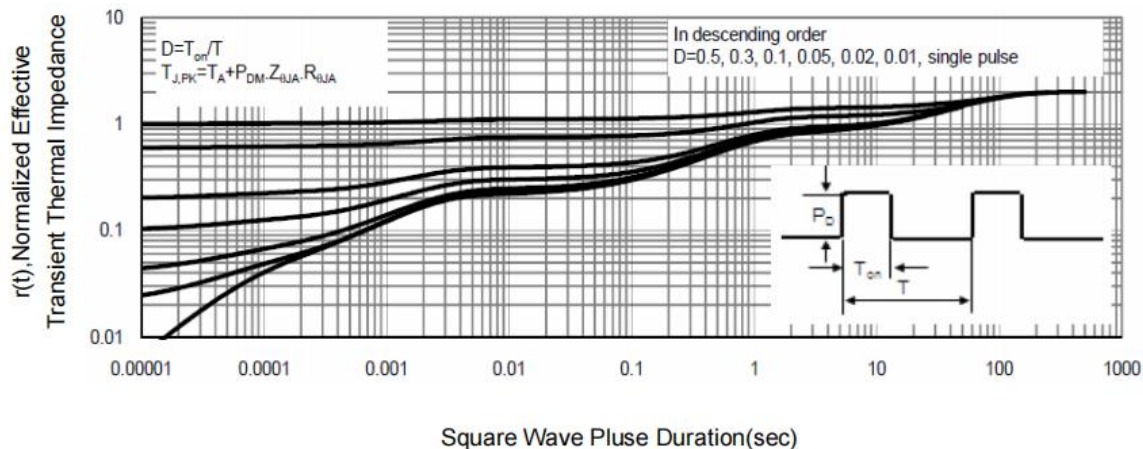
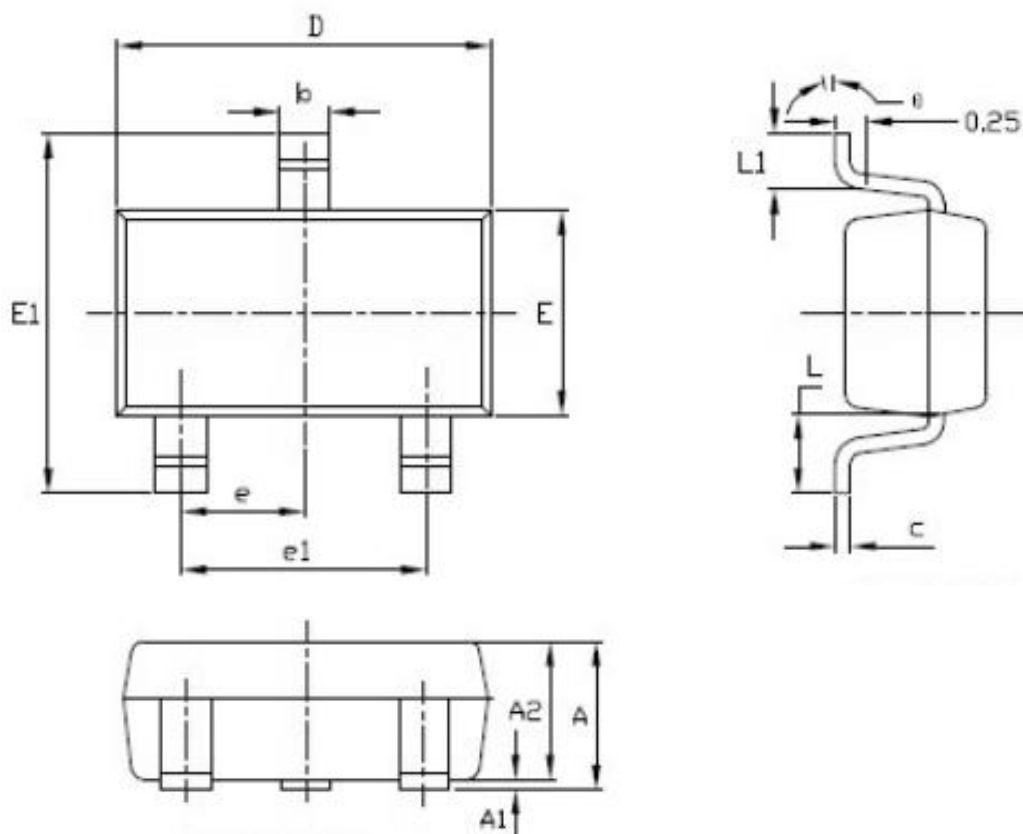


Figure 10: Transient Thermal Response Curve

■ Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.600REF		0.024REF	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°